

● General Description

The AGM2319EL combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

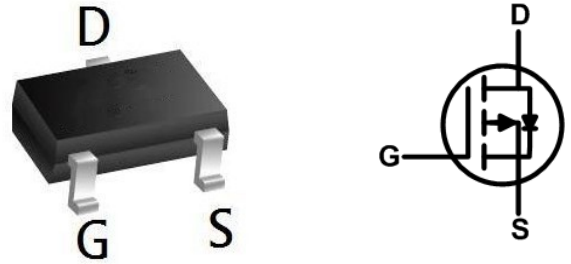
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-40V	63mΩ	-4A

SOT-23 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM2319	AGM2319EL	SOT-23	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-4.0	A
	Drain Current-Continuous(Tc=100°C)	--	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-20	A
PD	Maximum Power Dissipation(Tc=25°C)	1.2	w
	Maximum Power Dissipation(Tc=100°C)	0.48	w
EAS	Avalanche energy (Note 3)	--	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	104	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	--	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

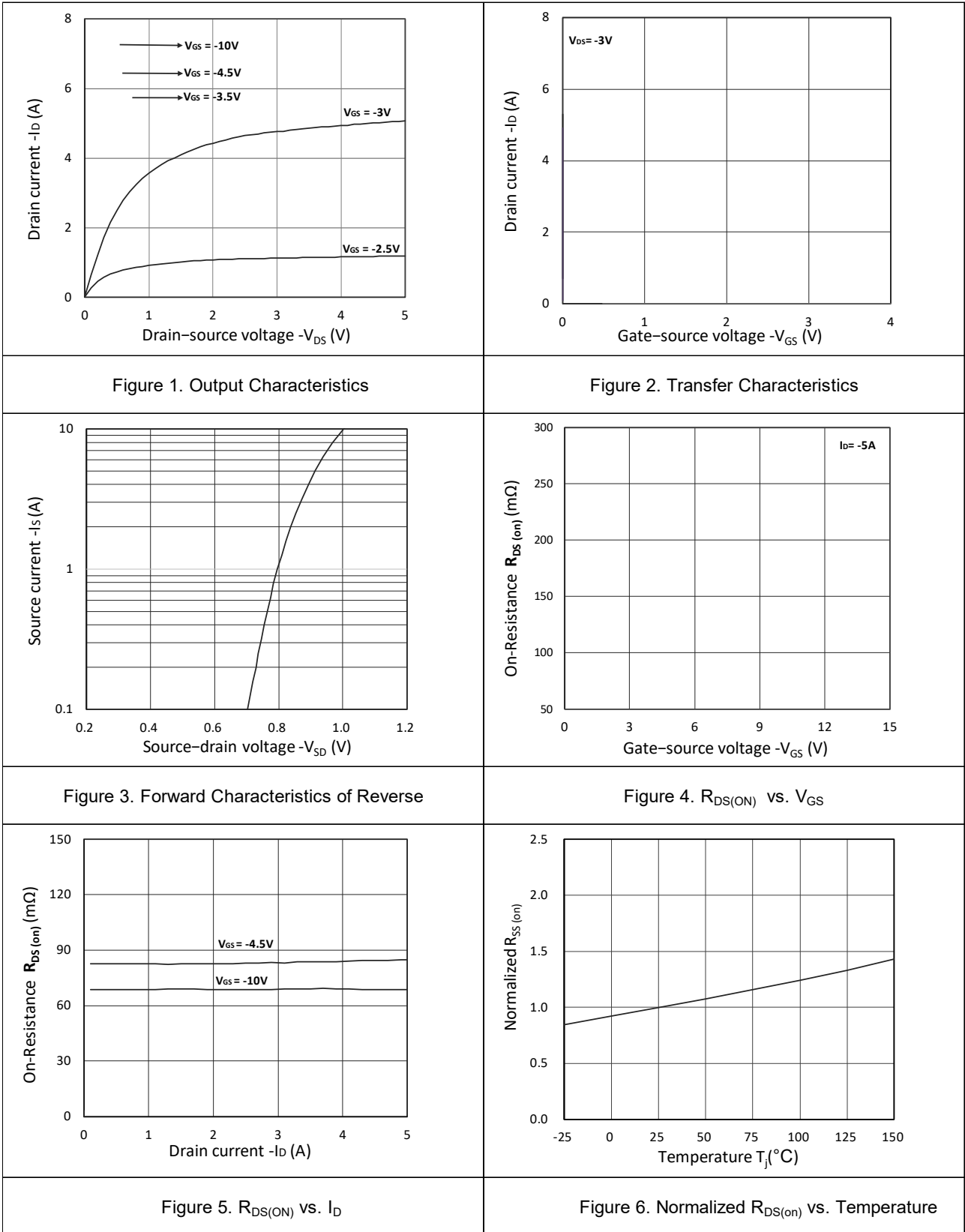
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	-40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-40V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.5	-2.5	V
gFS	Forward Transconductance	VDS=-10V,ID=-2A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-5A	--	63	85	mΩ
		VGS=-4.5V, ID=-4A	--	50	125	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-20V,VGS=0V, F=1MHZ	--	553	--	pF
Coss	Output Capacitance		--	50	--	pF
Crss	Reverse Transfer Capacitance		--	42	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHZ	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-20V, RL=2.5Ω,RGEN=3Ω	--	7.0	--	nS
tr	Turn-on Rise Time		--	6.5	--	nS
td(off)	Turn-Off Delay Time		--	24	--	nS
tf	Turn-Off Fall Time		--	7.8	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-20V, ID=-5A	--	11.8	--	nC
Qgs	Gate-Source Charge		--	2.2	--	nC
Qgd	Gate-Drain Charge		--	3.0	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-4.0	A
VSD	Forward on Voltage	VGS=0V,IS=-5A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-5A , dl/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

Typical Characteristics



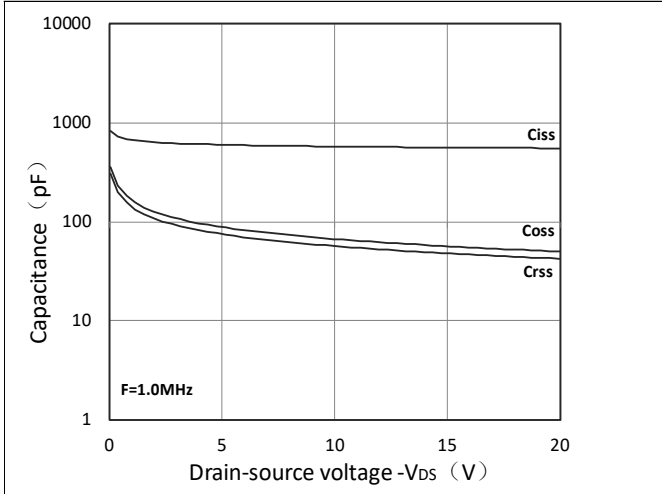


Figure 7. Capacitance Characteristics

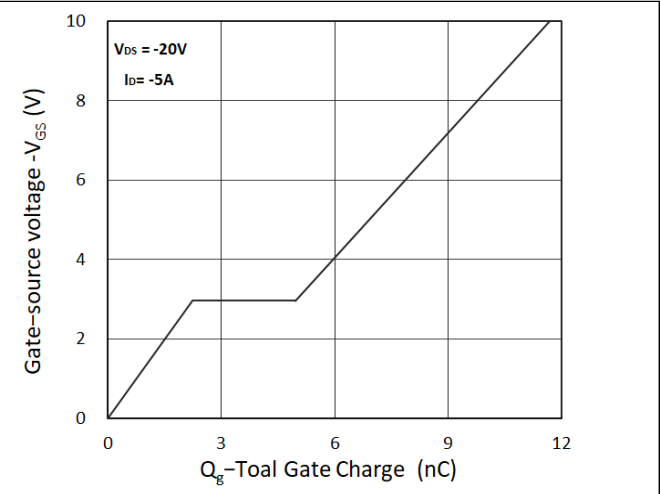
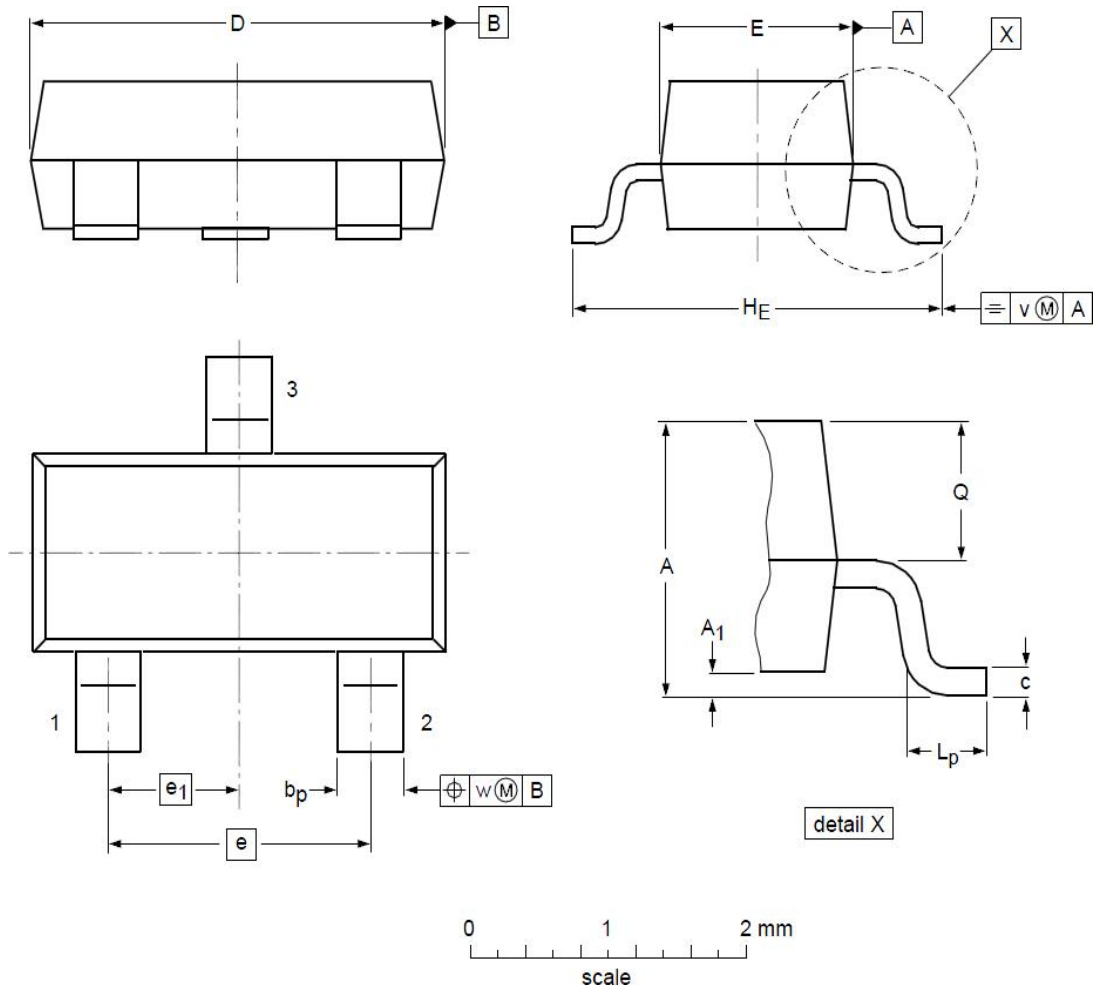


Figure 8. Gate Charge Characteristics

Package Mechanical Data-SOT-23



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A₁	0.01	0.05	0.10
b_p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e₁	--	0.95	--
H_E	2.25	2.40	2.55	L_p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				


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